PROCESS FOR PRODUCING SEMICONDUCTOR DEVICE

ABSTRACT

The first process for producing a semiconductor device according to the invention comprises the steps of:

providing a wafer of given thickness having a surface furnished with semiconductor circuits and a back;

forming grooves of a cut depth smaller than the thickness of the wafer, said grooves extending from the wafer circuit surface;

sticking a surface protective sheet onto the wafer circuit surface;

grinding the back of the wafer so that the thickness of the wafer is reduced to thereby finally result in division of the wafer into individual chips with spaces therebetween;

sticking a pressure sensitive adhesive sheet for pickup step onto the ground back of the wafer, said pressure sensitive adhesive sheet for pickup step comprising a base and, superimposed thereon, an energy radiation curable pressure sensitive adhesive layer;

exposing the energy radiation curable pressure sensitive adhesive layer to an energy radiation; and

peeling the surface protective sheet from the wafer circuit surface. This process is advantageous in

that chip alignment is excellent to thereby enable enhancing chip pickup efficiency.

FIGURE 4.